RoHS



STW9C2PB-S - Mid-Power LED



Actualize a spectrum closest to the sunlight

Mid-Power LED – 3030 Series

STW9C2PB-S (Cool, Neutral, Warm)



Product Brief

Description

- This White Colored surface-mount LED comes in standard package dimension. Package Size : 3.0x3.0x0.6mm
- It has a substrate made up of a molded plastic reflector sitting on top of a lead frame.
- The die is attached within the reflector cavity and the cavity is encapsulated by silicone.
- The package design coupled with careful selection of component materials allow these products to perform with high reliability.

Features and Benefits

- Thermally Enhanced Package Design
- Mid Power to High Power up to 0.2W
- Max. Driving Current 150mA
- Compact Package Size
- High Color Quality with CRI Min.95 (R9>85)
- Pb-free Reflow Soldering Application
- Eye Safety (Exempt 5000K)

Key Applications

- Replacement lamps Bulb, Tube
- Commercial
- Industrial
- Residential

Table 1. Product Selection Table

Part Number		C	ст	
Part Number	Color	Min.	Тур.	Max.
	Cool White	4700K	5600K	7000K
STW9C2PB-S	Neutral White	3700K	4200K	4700K
	Warm White	2600K	3000K	3700K



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Performance Characteristics

	ССТ (К) ^[1]		Luminous	Intensity ^[2]	Luminou	s Flux ^[3]	CRI
Part Number		RANK	l _v (cd)	Φν	(Im)	Ra
	Тур.		Min	Max	Min	Max	Min.
		P0	6.0	6.5	19.0	20.6	95
	6500	P5	6.5	7.0	20.6	22.2	95
		Q0	7.0	7.5	22.2	23.8	95
		P0	6.0	6.5	19.0	20.6	95
	5700	P5	6.5	7.0	20.6	22.2	95
		Q0	7.0	7.5	22.2	23.8	95
		P0	6.0	6.5	19.0	20.6	95
	5000	P5	6.5	7.0	20.6	22.2	95
STW9C2PB-S		Q0	7.0	7.5	22.2	23.8	95
		P0	6.0	6.5	18.9	20.5	95
	4000	P5	6.5	7.0	20.5	22.1	95
	-	Q0	7.0	7.5	22.1	23.6	95
		P0	6.0	6.5	18.6	20.2	95
3000	P5	6.5	7.0	20.2	21.7	95	
	-	Q0	7.0	7.5	21.7	23.3	95
	0700	P0	6.0	6.5	18.6	20.2	95
	2700 -	P5	6.5	7.0	20.2	21.7	95

Table 2. Product Selection Guide, $I_F = 65mA$, $T_i = 25^{\circ}C$, RH30%

Notes :

- (1) Correlated Color Temperature is derived from the CIE 1931 Chromaticity diagram.
- (2) Seoul Semiconductor maintains a tolerance of ±5% on Intensity and power measurements. The luminous intensity IV was measured at the peak of the spatial pattern which may not be aligned with the mechanical axis of the LED package.
- (3) The lumen table is only for reference.



Performance Characteristics

Parameter	Symbol		Value		Unit
Farallieter	Symbol	Min.	Тур.	Max.	Onit
Forward Current	I _F	-	65	-	mA
Forward Voltage ^[1]	V _F	2.9	-	3.2	V
Luminous Intensity (5000K) ^[1]	١ _v	-	6.9 (21.9)	-	cd (Im)
CRI ^[1]	R _a	95	-	-	
Viewing Angle ^[2]	2Θ _{1/2}	-	120	-	Deg.
Thermal resistance (J to S) [3]	$R\theta_{J-S}$	-	10	-	°C/W
ESD Sensitivity(HBM)	-	Class 3A JESD22-A114-E			

Table 4. Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Forward Current	I _F	150	mA
Power Dissipation	P _D	0.48	W
Junction Temperature	Τ _j	125	°C
Operating Temperature	T _{opr}	-40~ + 85	°C
Storage Temperature	T _{stg}	-40 ~ + 100	٥C

Notes :

- (1) Tolerance : VF :±0.1V, IV :±5%, Ra :±2, x,y :±0.005
- (2) $2\Theta_{1/2}$ is the off-axis where the luminous intensity is 1/2 of the peak intensity.
- (3) Thermal resistance : Rth_{JS} (Junction / solder)
- · LED's properties might be different from suggested values like above and below tables if operation condition will be exceeded our parameter range. Care is to be taken that power dissipation does not exceed the absolute maximum rating of the product.
- Thermal resistance can be increased substantially depending on the heat sink design/operating condition, and the maximum possible driving current will decrease accordingly.
- All measurements were made under the standardized environment of Seoul Semiconductor. .



Characteristics Graph

Fig 1. Color Spectrum, T_i = 25°C

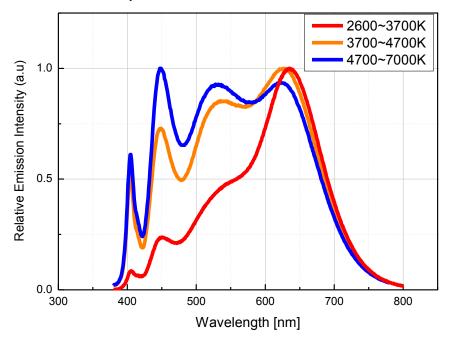
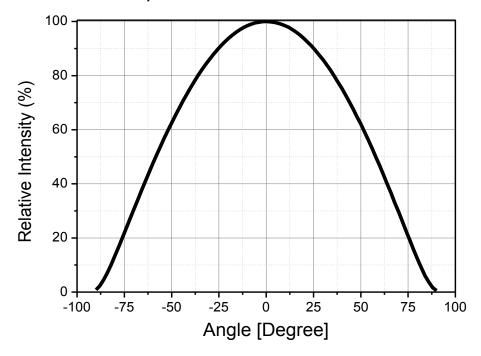


Fig 2. Radiant Pattern, T_i = 25°C





Characteristics Graph

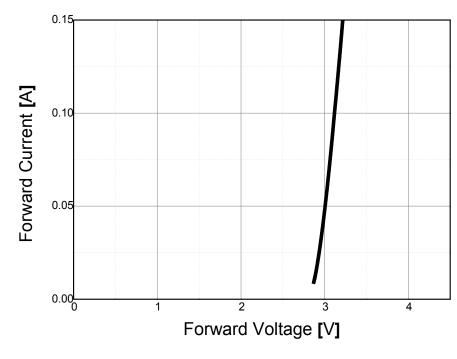
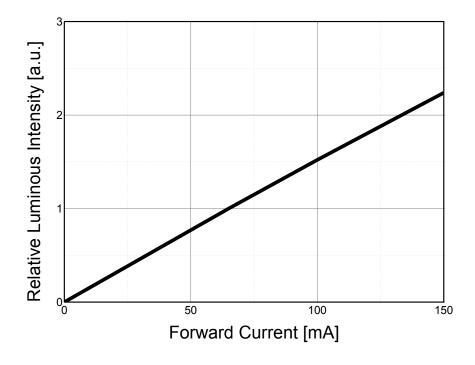


Fig 3. Forward Voltage vs. Forward Current, $T_j = 25^{\circ}C$

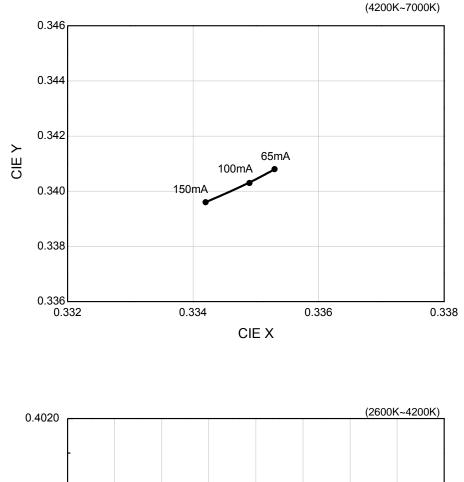
Fig 4. Forward Current vs. Relative Luminous Intensity, T_j = 25°C

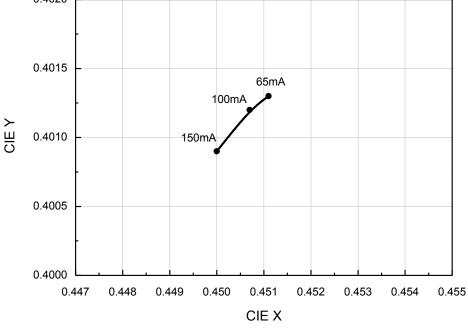




Characteristics Graph

Fig 5. Forward Current vs. CIE X, Y Shift, T_i = 25°C







Characteristics Graph

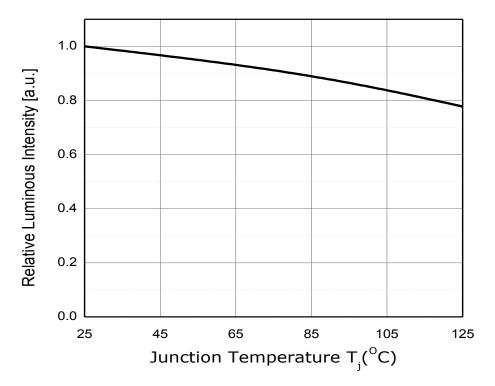
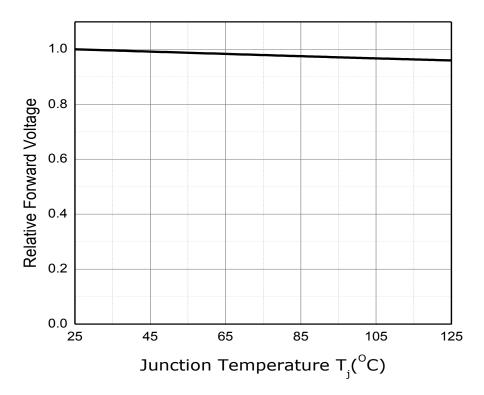


Fig 6. Junction Temperature vs. Relative Luminous Intensity, I_F =65mA

Fig 7. Junction Temperature vs. Relative Forward Voltage, I_F=65mA





(2600K~4200K)

Characteristics Graph

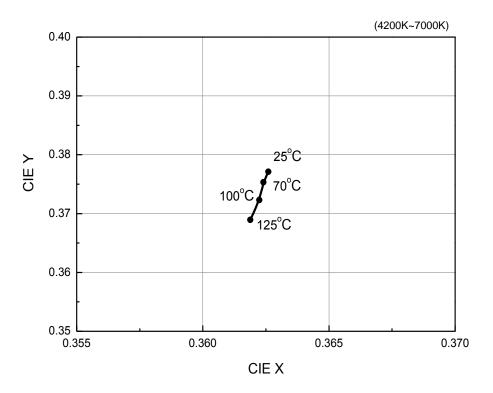
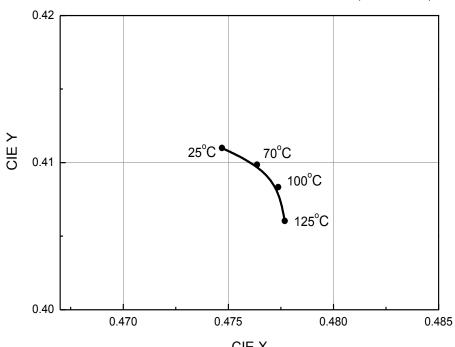


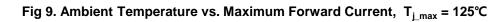
Fig 8. Chromaticity Coordinate vs. Junction Temperature, I_F =65mA

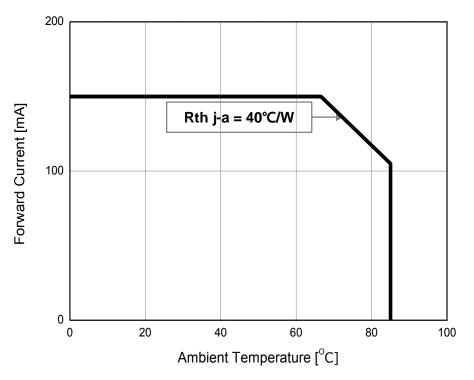






Characteristics Graph







Color Bin Structure

Table 5. Bin Code description, $T_j=25^{\circ}C$, $I_F=65mA$

Part Number	Lumin	ous Intensi	ty (cd)	Color Chromaticity	Typical Forward Voltage (V)			
Part Number	Bin Code	Min.	Max.	Coordinate	Bin Code	Min.	Max.	
	P0	6.0	6.5		Y3	2.9	3.0	
STW9C2PB-S	P5	6.5	7.0		Z1	3.0	3.1	
3100902PB-3	Q0	7.0	7.5		Z2	3.1	3.2	
	Q5	7.5	8.0					

Table 6. Intensity rank distribution

Available ranks

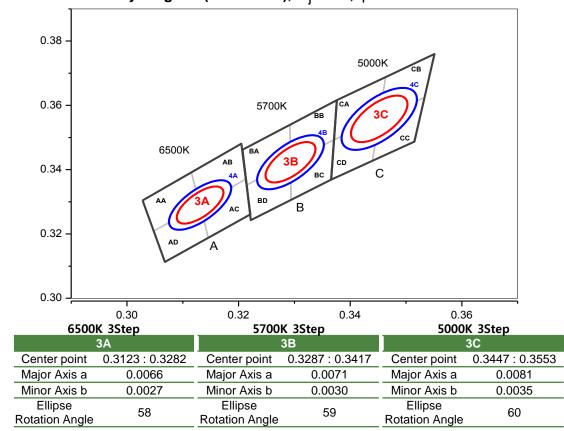
сст	CIE		IV R	lank	
6000 ~ 7000K	А	P0	P5	Q0	Q5
5300 ~ 6000K	В	P0	P5	Q0	Q5
4700 ~ 5300K	С	P0	P5	Q0	Q5
3700 ~ 4200K	Е	P0	P5	Q0	Q5
2900 ~ 3200K	G	P0	P5	Q0	Q5
2600 ~ 2900K	Н	P0	P5	Q0	Q5

*Notes :

All measurements were made under the standardized environment of Seoul Semiconductor. In order to ensure availability, single color rank will not be orderable.



Color Bin Structure



CIE Chromaticity	/ Diagram	(Cool white)	T _i =25℃, I _F =65mA
			$I_i = 2J C_i I_F = 0JIIIA$

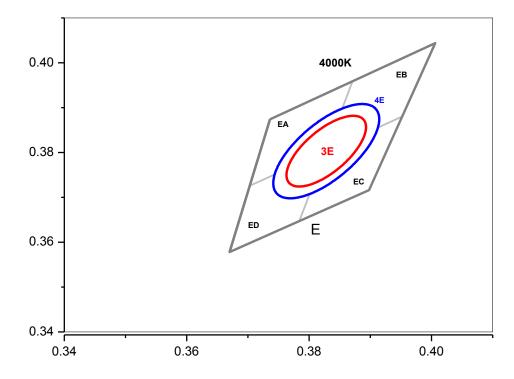
6500K 4Step		5700	K 4Step	5000K 4Step		
	4A	4B		4C		
Center point	0.3123 : 0.3282	Center point	0.3287 : 0.3417	Center point	0.3447 : 0.3553	
Major Axis a	0.0088	Major Axis a	0.0095	Major Axis a	0.0108	
Minor Axis b	0.0036	Minor Axis b	0.0040	Minor Axis b	0.0047	
Ellipse Rotation Angle	58	Ellipse Rotation Angle	59	Ellipse Rotation Angle	60	

A	A	A	В	A	С	A	D
CIE X	CIE Y						
0.3028	0.3304	0.3115	0.3393	0.3131	0.329	0.3048	0.3209
0.3048	0.3209	0.3131	0.329	0.3146	0.3187	0.3068	0.3113
0.3131	0.329	0.3213	0.3371	0.3221	0.3261	0.3146	0.3187
0.3115	0.3393	0.3205	0.3481	0.3213	0.3371	0.3131	0.329
В	A	В	В	В	С	В	D
CIE X	CIE Y						
0.3207	0.3462	0.3292	0.3539	0.3293	0.3423	0.3215	0.3353
0.3215	0.3353	0.3293	0.3423	0.3294	0.3306	0.3222	0.3243
0.3293	0.3423	0.3371	0.3493	0.3366	0.3369	0.3294	0.3306
0.3292	0.3539	0.3376	0.3616	0.3371	0.3493	0.3293	0.3423
C	A	C	В	C	C	C	D
CIE X	CIE Y						
0.3376	0.3616	0.3463	0.3687	0.3452	0.3558	0.3371	0.3493
0.3371	0.3493	0.3452	0.3558	0.344	0.3428	0.3366	0.3369
0.3452	0.3558	0.3533	0.3624	0.3514	0.3487	0.344	0.3428
0.3463	0.3687	0.3551	0.376	0.3533	0.3624	0.3452	0.3558



Color Bin Structure

CIE Chromaticity Diagram (Cool white), $T_j=25^{\circ}C$, $I_F=65mA$



4000K 3Step					
3E					
Center point	0.3818 : 0.3797				
Major Axis a	0.0094				
Minor Axis b	0.0040				
Ellipse	53				
Rotation Angle	55				

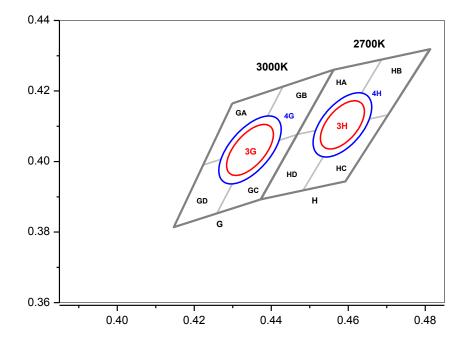
4000K 4Step				
4E				
Center point	0.3818 : 0.3797			
Major Axis a	0.0125			
Minor Axis b	0.0053			
Ellipse	53			
Rotation Angle				

E	A	E	В	E	c	E	D
CIE X	CIE Y						
0.3736	0.3874	0.3871	0.3959	0.3828	0.3803	0.3703	0.3726
0.3703	0.3726	0.3828	0.3803	0.3784	0.3647	0.367	0.3578
0.3828	0.3803	0.3952	0.388	0.3898	0.3716	0.3784	0.3647
0.3871	0.3959	0.4006	0.4044	0.3952	0.388	0.3828	0.3803



Color Bin Structure

CIE Chromaticity Diagram (Cool white), T_i=25°C, I_F=65mA



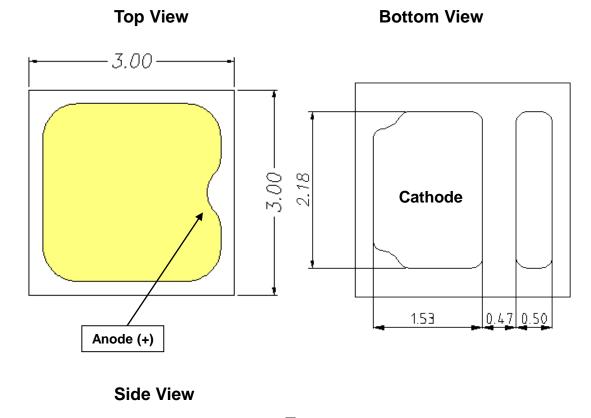
3000	K 3Step	2700K 3Step		
3	Step	3 Step		
Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101	
Major Axis a	0.0085	Major Axis a	0.0079	
Minor Axis b	0.0041	Minor Axis b	0.0041	
Ellipse Rotation Angle	53	Ellipse Rotation Angle	54	

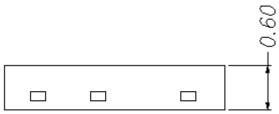
3000	K 4Step	2700K 4Step		
4	Step	4 Step		
Center point	0.4338 : 0.4030	Center point	0.4578 : 0.4101	
Major Axis a	0.0113	Major Axis a	0.0105	
Minor Axis b	0.0055	Minor Axis b	0.0055	
Ellipse	53	Ellipse	54	
Rotation Angle	55	Rotation Angle		

G	A	G	В	G	c	G	D
CIE X	CIE Y						
0.4299	0.4165	0.443	0.4212	0.4345	0.4033	0.4223	0.399
0.4223	0.399	0.4345	0.4033	0.4259	0.3853	0.4147	0.3814
0.4345	0.4033	0.4468	0.4077	0.4373	0.3893	0.4259	0.3853
0.443	0.4212	0.4562	0.426	0.4468	0.4077	0.4345	0.4033
н	A	н	В	н	c	н	D
CIE X	CIE Y						
0.4562	0.426	0.4687	0.4289	0.4585	0.4104	0.4468	0.4077
0.4468	0.4077	0.4585	0.4104	0.4483	0.3919	0.4373	0.3893
0.4585	0.4104	0.4703	0.4132	0.4593	0.3944	0.4483	0.3919
0.4687	0.4289	0.481	0.4319	0.4703	0.4132	0.4585	0.4104



Mechanical Dimensions

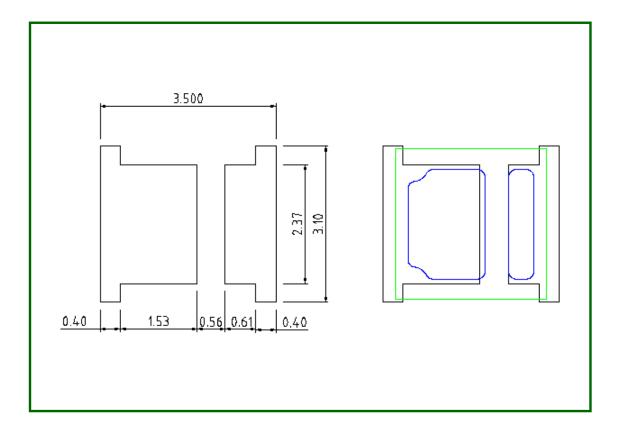




- (1) All dimensions are in millimeters.
- (2) Scale : none
- (3) Undefined tolerance is ± 0.2 mm



Recommended Solder Pad



Notes :

- (1) All dimensions are in millimeters.
- (2) Scale : none
- (3) This drawing without tolerances are for reference only
- (4) Undefined tolerance is ± 0.1 mm



Reflow Soldering Characteristics

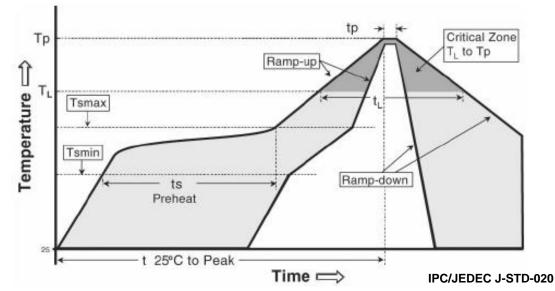


Table 7.

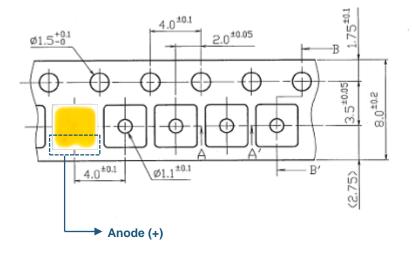
Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate (Tsmax to Tp)	3° C/second max.	3° C/second max.
Preheat - Temperature Min (Tsmin) - Temperature Max (Tsmax) - Time (Tsmin to Tsmax) (ts)	100 °C 150 °C 60-120 seconds	150 ℃ 200 ℃ 60-180 seconds
Time maintained above: - Temperature (TL) - Time (tL)	183 °C 60-150 seconds	217 °C 60-150 seconds
Peak Temperature (Tp)	215℃	260°C
Time within 5°C of actual Peak Temperature (tp)2	10-30 seconds	20-40 seconds
Ramp-down Rate	6 °C/second max.	6 °C/second max.
Time 25°C to Peak Temperature	6 minutes max.	8 minutes max.

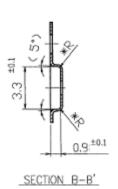
Caution

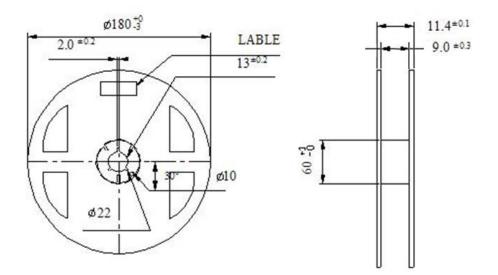
- (1) Reflow soldering is recommended not to be done more than two times. In the case of more than 24 hours passed soldering after first, LEDs will be damaged.
- (2) Repairs should not be done after the LEDs have been soldered. When repair is unavoidable, suitable tools must be used.
- (3) Die slug is to be soldered.
- (4) When soldering, do not put stress on the LEDs during heating.
- (5) After soldering, do not warp the circuit board.



Emitter Tape & Reel Packing





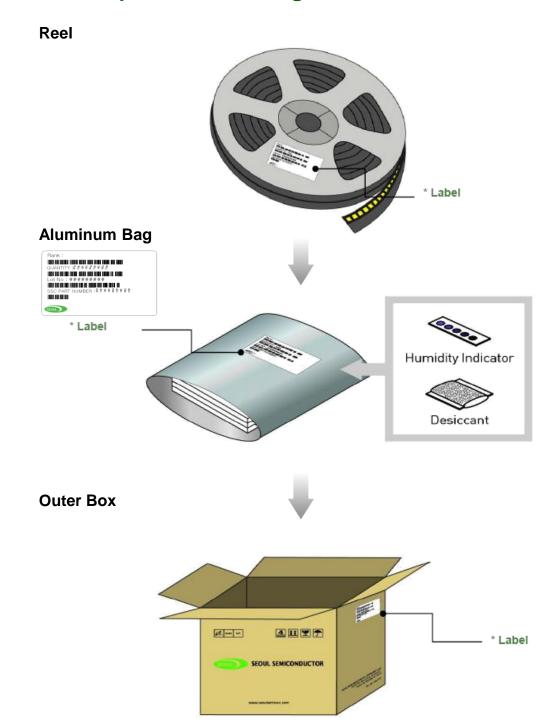


(Tolerance: ± 0.2 , Unit: mm)

- (1) Quantity: 4,500pcs/Reel
- (2) Cumulative Tolerance : Cumulative Tolerance/10 pitches to be \pm 0.2mm
- (3) Adhesion Strength of Cover Tape
- Adhesion strength to be 0.1-0.7N when the cover tape is turned off from the carrier tape at the angle of 10° to the carrier tape.
- (4) Package : P/N, Manufacturing data Code No. and Quantity to be indicated on a damp proof Package.



Emitter Tape & Reel Packing



SUNLIKE SEOUL SEMICONDUCTOR

STW9C2PB-S - Mid-Power LED

Product Nomenclature

Part Number Code	Description	Part Number	Value
X ₁	Company	S	
X ₂	Top View LED series	Т	
X ₃ X ₄	Color Specification	W9 CRI 90	
X ₅	Package series	C C series	
X ₆ X ₇	Characteristic code	2P	
X ₈	Revision	В	
X ₉	Characteristic	S	Sunlike

Table 8. Part Numbering System : X₁X₂X₃X₄X₅X₆X₇X₈-X₉X₁₀

Table 9. Lot Numbering System $:Y_1Y_2Y_3Y_4Y_5Y_6Y_7Y_8Y_9Y_{10}-Y_{11}Y_{12}Y_{13}Y_{14}Y_{15}Y_{16}Y_{17}$

Lot Number Code	Description	Lot Number	Value
Y ₁ Y ₂	Year	Year	
Y ₃	Month		
Y ₄ Y ₅	Day		
Y ₆	Top View LED series		
Y ₇ Y ₈ Y ₉ Y ₁₀	Mass order		
Y ₁₁ Y ₁₂ Y ₁₃ Y ₁₄ Y ₁₅ Y ₁₆ Y ₁₇	Internal Number		

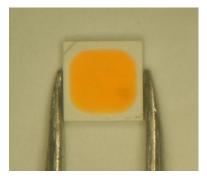


Handling of Silicone Resin for LEDs

(1) During processing, mechanical stress on the surface should be minimized as much as possible. Sharp objects of all types should not be used to pierce the sealing compound.



(2) In general, LEDs should only be handled from the side. By the way, this also applies to LEDs without a silicone sealant, since the surface can also become scratched.



(3) When populating boards in SMT production, there are basically no restrictions regarding the form of the pick and place nozzle, except that mechanical pressure on the surface of the resin must be prevented. This is assured by choosing a pick and place nozzle which is larger than the LED's reflector area.

(4) Silicone differs from materials conventionally used for the manufacturing of LEDs. These conditions must be considered during the handling of such devices. Compared to standard encapsulants, silicone is generally softer, and the surface is more likely to attract dust.

As mentioned previously, the increased sensitivity to dust requires special care during processing. In cases where a minimal level of dirt and dust particles cannot be guaranteed, a suitable cleaning solution must be applied to the surface after the soldering of components.

(5) SSC suggests using isopropyl alcohol for cleaning. In case other solvents are used, it must be assured that these solvents do not dissolve the package or resin. Ultrasonic cleaning is not recommended. Ultrasonic cleaning may cause damage to the LED.

(6) Please do not mold this product into another resin (epoxy, urethane, etc) and do not handle this. product with acid or sulfur material in sealed space.

LIKe seoul semiconductor



STW9C2PB-S - Mid-Power LED

Precaution for Use

(1) Storage

To avoid the moisture penetration, we recommend store in a dry box with a desiccant. The recommended storage temperature range is 5° C to 30° C and a maximum humidity of RH50%.

(2) Use Precaution after Opening the Packaging

Use proper SMT techniques when the LED is to be soldered dipped as separation of the lens may affect the light output efficiency.

Pay attention to the following:

- a. Recommend conditions after opening the package
 - Sealing
 - Temperature : 5 ~ 30°C Humidity : less than RH60%
- b. If the package has been opened more than 4 week(MSL_2a) or the color of the desiccant changes, components should be dried for 10-24hr at $65\pm5^\circ$ C
- (3) Do not apply mechanical force or excess vibration during the cooling process to normal temperature after soldering.
- (4) Do not rapidly cool device after soldering.
- (5) Components should not be mounted on warped (non coplanar) portion of PCB.
- (6) Radioactive exposure is not considered for the products listed here in.
- (7) Gallium arsenide is used in some of the products listed in this publication.These products are dangerous if they are burned or shredded in the process of disposal.It is also dangerous to drink the liquid or inhale the gas generated by such products when chemically disposed of.
- (8) This device should not be used in any type of fluid such as water, oil, organic solvent and etc. When washing is required, IPA (Isopropyl Alcohol) should be used.
- (9) When the LEDs are in operation the maximum current should be decided after measuring the package temperature.



Precaution for Use

- (10) The appearance and specifications of the product may be modified for improvement without notice.
- (11) Long time exposure of sunlight or occasional UV exposure will cause lens discoloration.
- (12) VOCs (Volatile organic compounds) emitted from materials used in the construction of fixtures can penetrate silicone encapsulants of LEDs and discolor when exposed to heat and photonic energy. The result can be a significant loss of light output from the fixture. Knowledge of the properties of the materials selected to be used in the construction of fixtures can help prevent these issues.
- (13) Attaching LEDs, do not use adhesives that outgas organic vapor.
- (14) The driving circuit must be designed to allow forward voltage only when it is ON or OFF. If the reverse voltage is applied to LED, migration can be generated resulting in LED damage.
- (15) Similar to most Solid state devices;

LEDs are sensitive to Electro-Static Discharge (ESD) and Electrical Over Stress (EOS). Below is a list of suggestions that Seoul Semiconductor purposes to minimize these effects.

a. ESD (Electro Static Discharge)

Electrostatic discharge (ESD) is the defined as the release of static electricity when two objects come into contact. While most ESD events are considered harmless, it can be an expensive problem in many industrial environments during production and storage. The damage from ESD to an LEDs may cause the product to demonstrate unusual characteristics such as:

- Increase in reverse leakage current lowered turn-on voltage
- Abnormal emissions from the LED at low current

The following recommendations are suggested to help minimize the potential for an ESD event. One or more recommended work area suggestions:

- Ionizing fan setup
- ESD table/shelf mat made of conductive materials
- ESD safe storage containers

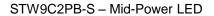
One or more personnel suggestion options:

- Antistatic wrist-strap
- Antistatic material shoes
- Antistatic clothes

Environmental controls:

- Humidity control (ESD gets worse in a dry environment)







Precaution for Use

b. EOS (Electrical Over Stress)

Electrical Over-Stress (EOS) is defined as damage that may occur when an electronic device is subjected to a current or voltage that is beyond the maximum specification limits of the device. The effects from an EOS event can be noticed through product performance like:

- Changes to the performance of the LED package

(If the damage is around the bond pad area and since the package is completely encapsulated the package may turn on but flicker show severe performance degradation.)

- Changes to the light output of the luminaire from component failure
- Components on the board not operating at determined drive power

Failure of performance from entire fixture due to changes in circuit voltage and current across total circuit causing trickle down failures. It is impossible to predict the failure mode of every LED exposed to electrical overstress as the failure modes have been investigated to vary, but there are some common signs that will indicate an EOS event has occurred:

- Damaged may be noticed to the bond wires (appearing similar to a blown fuse)
- Damage to the bond pads located on the emission surface of the LED package
- (shadowing can be noticed around the bond pads while viewing through a microscope)
- Anomalies noticed in the encapsulation and phosphor around the bond wires.
- This damage usually appears due to the thermal stress produced during the EOS event.

c. To help minimize the damage from an EOS event Seoul Semiconductor recommends utilizing:

- A surge protection circuit
- An appropriately rated over voltage protection device
- A current limiting device